

## Features

- Low drain-source on-resistance:  $R_{DS(ON)}=0.318\Omega(\text{typ})$
- Easy to control gate switching
- Enhancement mode:  $V_{th} = 2.8$  to  $4.2V$
- 100% avalanche tested
- RoHS compliant

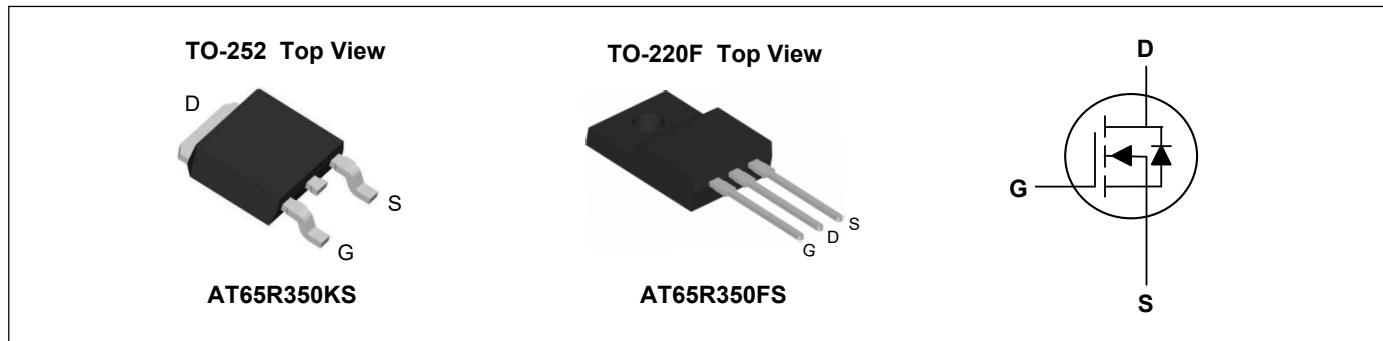
## Key Performance Parameters



Parameter	Value	Unit
$V_{DS} @ T_{j,\max}$	650	V
$R_{DS(ON),\max}$	350	mΩ
$I_D$	11	A
$Q_{g,\text{typ}}$	22	nC
$I_{DM}$	33	A

## Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charger, Lighting.



## Absolute Maximum Ratings( $T_c=25^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	TO-252	TO-220F	Unit
Drain-Source Voltage	$V_{DS}$	650		V
Gate-Source Voltage	$V_{GS}$	$\pm 30$		V
Continuous Drain Current <sup>1</sup>	$I_D @ T_c=25^\circ\text{C}$	11		A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	33		A
Single Pulse Avalanche Energy	EAS	624		mJ
MOSFET dv/dt ruggedness, $V_{DS} = 0 \dots 400V$	dv/dt	69		V/ns
Reverse diode dv/dt <sup>3</sup> $V_{DS}=0 \dots 400V$ , $I_{SD} \leq 48A$ , $T_j=25^\circ\text{C}$		15		
Total Power Dissipation ( $T_c=25^\circ\text{C}$ )	$P_D$	83	31	W
Storage Temperature Range	$T_{STG}$	-55 to 150		°C
Operating Junction Temperature Range	$T_J$	-55 to 150		°C

## Thermal Characteristics

Parameter	Symbol	TO-252	TO-220F	Unit
		Max	Max	
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	62	80	°C/W
Thermal Resistance Junction-Case	$R_{\theta JC}$	1.5	4	°C/W

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}$ , $I_D=10\text{mA}$	655	---	---	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$ , $I_D=5.5\text{A}$	---	318	350	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$ , $I_D=250\text{\mu A}$	2.8	---	4.2	V
Drain-Source Leakage Current	$I_{\text{DSS}}$	$V_{\text{DS}}=650\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=25^\circ\text{C}$	---	---	100	nA
Gate-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 30\text{V}$ , $V_{\text{DS}}=0\text{V}$	---	---	$\pm 100$	nA
Gate Resistance	$R_G$	$f = 1.0\text{MHz}$ , open drain	---	11	---	$\Omega$
Total Gate Charge	$Q_g$	$V_{\text{DD}}=400\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $I_D=4.8\text{A}$	---	22	---	nC
Gate-Source Charge	$Q_{\text{gs}}$		---	5.8	---	
Gate-Drain Charge	$Q_{\text{gd}}$		---	17	---	
Gate Plateau Voltage	$V_{\text{plateau}}$		---	5.3	---	V
Turn-On Delay Time	$T_{\text{d(on)}}$	$V_{\text{DD}}=400\text{V}$ , $V_{\text{GS}}=13\text{V}$ , $R_G=3.4\Omega$ , $I_D=4.8\text{A}$	---	7.2	---	ns
Rise Time	$T_r$		---	20.8	---	
Turn-Off Delay Time	$T_{\text{d(off)}}$		---	29.2	---	
Fall Time	$T_f$		---	19.2	---	
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=50\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	901	---	pF
Output Capacitance	$C_{\text{oss}}$		---	59	---	
Reverse Transfer Capacitance	$C_{\text{rss}}$		---	5.3	---	

**Drain-Source Diode Characteristics**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode Forward Voltage	$V_{\text{SD}}$	$V_{\text{G}}=0\text{V}$ , $I_F=1\text{A}$ , $T_J=25^\circ\text{C}$	---	0.74	---	V
Reverse Recovery Time	$t_{\text{rr}}$	$V_R=400\text{V}$ , $I_F=4.8\text{ A}$ , $dI_F/dt=100\text{A}/\mu\text{s}$	---	250	---	ns
Reverse Recovery Charge	$Q_{\text{rr}}$		---	2.572	---	uC
Peak Reverse Recovery Current	$I_{\text{rrm}}$		---	19.6	---	A

**Note:**

1. Limited by  $T_{j,\text{max}}$ . Maximum Duty Cycle D = 0.50
2. Pulse width  $t_p$  limited by  $T_{j,\text{max}}$
3. Identical low side and high side switch with identical  $R_G$

## Test Circuits

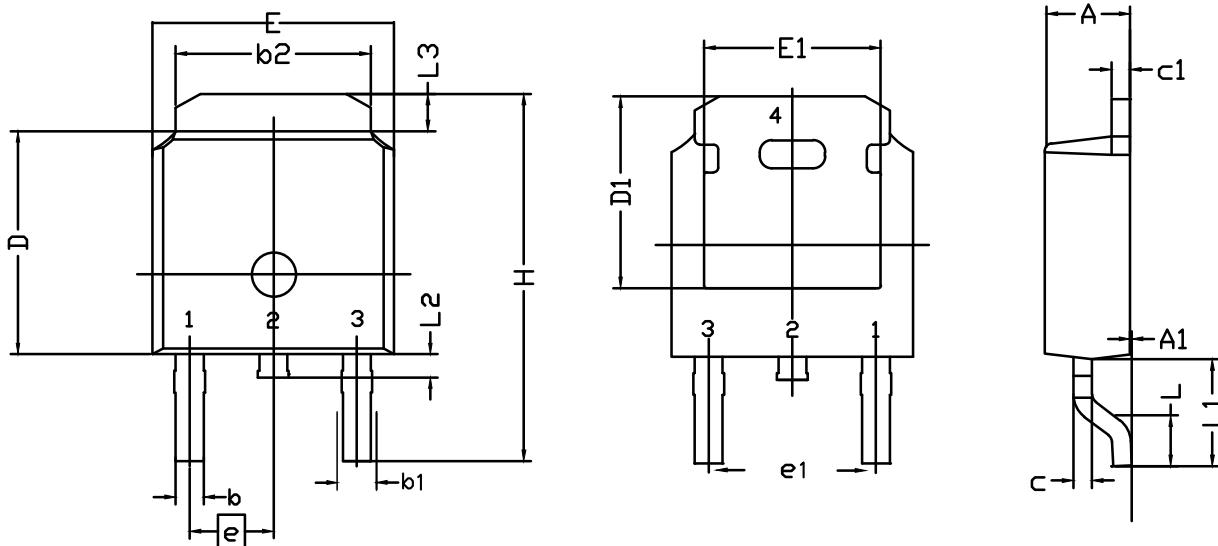
Test circuit for diode characteristics	Diode recovery waveform
 $R_{G1} = R_{G2}$	<p>Diode recovery waveform graph showing current <math>i</math> and voltage <math>V</math> versus time <math>t</math>. The graph illustrates the recovery process from forward current <math>I_F</math> through recovery time <math>t_R</math> to reverse recovery charge <math>Q_{rr} = Q_s + Q_f</math>. Key points marked include <math>t_s</math>, <math>t_f</math>, <math>10\% I_{RRM}</math>, and <math>90\% I_{RRM}</math>.</p>

## Switching times

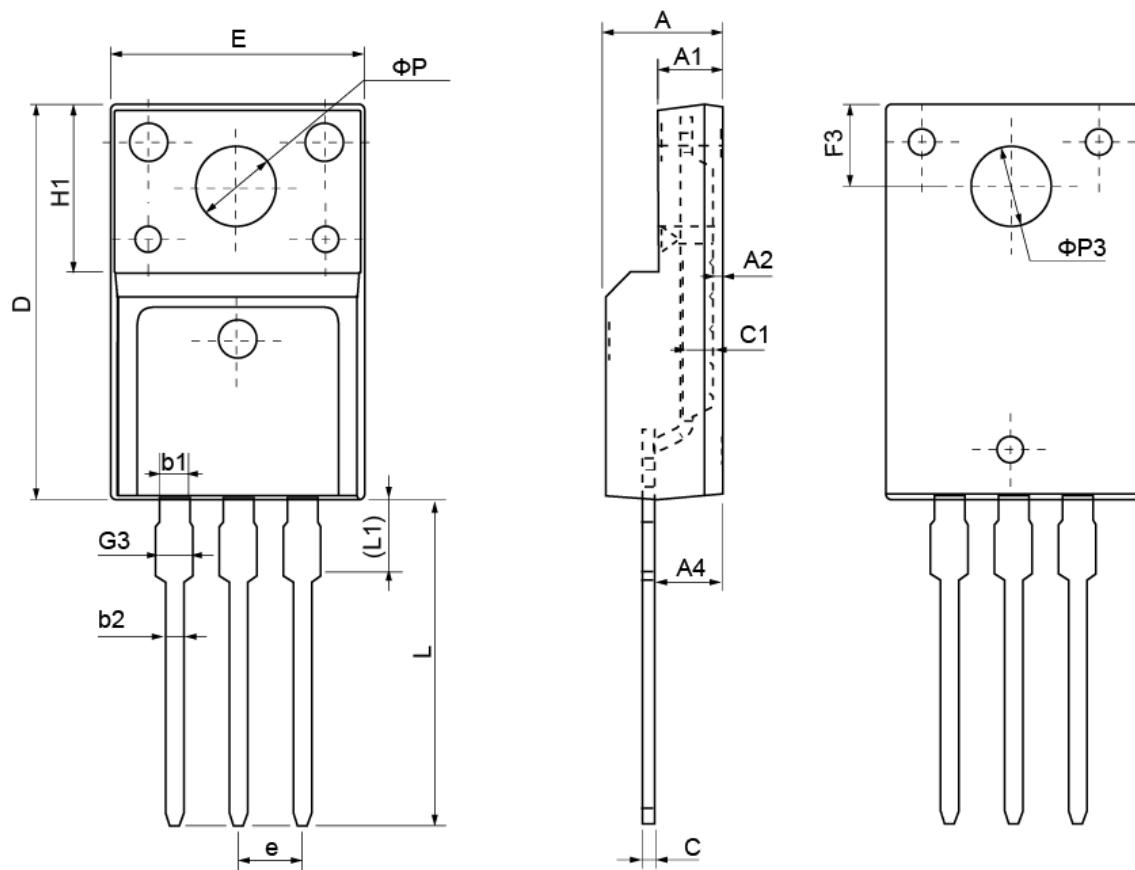
Switching times test circuit for inductive load	Switching times waveform

## Unclamped inductive load

Unclamped inductive load test circuit	Unclamped inductive waveform

**TO-252 Package Outline Dimensions**


<b>Symbol</b>	<b>Dimensions (unit:mm)</b>			<b>Symbol</b>	<b>Dimensions (unit:mm)</b>		
	<b>Min</b>	<b>Typ</b>	<b>Max</b>		<b>Min</b>	<b>Typ</b>	<b>Max</b>
<b>A</b>	2.20	2.30	2.38	<b>E</b>	6.40	6.60	6.731
<b>A<sub>1</sub></b>	0.00	0.10	0.20	<b>E<sub>1</sub></b>	4.40	--	--
<b>b</b>	0.64	0.76	0.89	<b>e</b>	2.286 BSC		
<b>b<sub>1</sub></b>	0.77	0.85	1.14	<b>e<sub>1</sub></b>	4.572 BSC		
<b>b<sub>2</sub></b>	5.00	5.33	5.46	<b>H</b>	9.40	10.00	10.40
<b>c</b>	0.458	0.508	0.610	<b>L</b>	1.40	1.52	1.77
<b>C<sub>1</sub></b>	0.458	0.508	0.620	<b>L<sub>1</sub></b>	--	2.743	--
<b>D</b>	5.98	6.10	6.223	<b>L<sub>2</sub></b>	0.60	0.80	1.01
<b>D<sub>1</sub></b>	5.20	5.25	5.38	<b>L<sub>3</sub></b>	0.90	1.06	1.25

**TO-220F Package Outline Dimensions**


<b>Symbol</b>	<b>Dimensions (unit:mm)</b>			<b>Symbol</b>	<b>Dimensions (unit:mm)</b>		
	<b>Min</b>	<b>Typ</b>	<b>Max</b>		<b>Min</b>	<b>Typ</b>	<b>Max</b>
<b>A</b>	4.40	4.70	5.00	<b>H1</b>	6.70 REF		
<b>A1</b>	2.30	2.55	2.80	<b>L</b>	12.30	12.98	13.30
<b>A2</b>	0.30	0.50	0.70	<b>L1</b>	2.95	3.10	3.50
<b>A4</b>	2.45	2.80	3.05	<b>φ P</b>	3.03	3.20	3.50
<b>c</b>	0.30	0.50	0.70	<b>φ P3</b>	3.15	3.45	3.65
<b>c1</b>	1.20	1.30	1.40	<b>b1</b>	1.10	1.30	1.45
<b>D</b>	15.40	15.90	16.40	<b>b2</b>	0.60	0.80	1.00
<b>E</b>	9.86	10.16	10.46	<b>F3</b>	3.05	3.30	3.55
<b>e</b>	2.54 BSC			<b>G3</b>	1.15	1.35	1.55